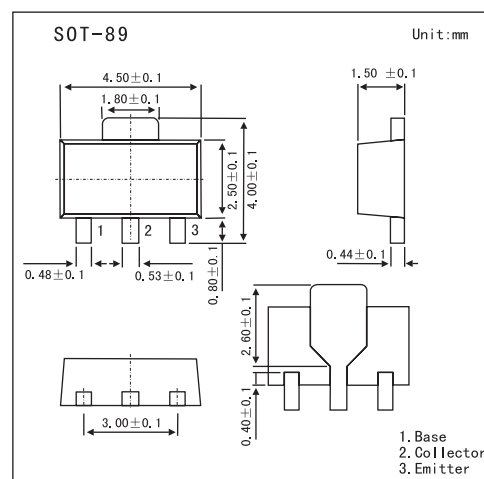


Silicon PNP Epitaxial

2SB1025

■ Features

- Low frequency power amplifier

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-120	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
peak collector current	I_{CP}^*1	-2	A
Collector power dissipation	P_C^*2	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

*1. $PW \leq 10 \text{ ms}$; $d \leq 0.02$.

*2. Value on the alumina ceramic board ($12.5 \square 20 \square 0.7 \text{ mm}$)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}$, $I_E = 0$	-120			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}$, $R_{BE} = \infty$	-80			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -100\text{V}$, $I_E = 0$			-10	μA
DC current transfer ratio	h_{FE}	$V_{CE} = -5 \text{ V}$, $I_C = -150 \text{ mA}$	60		320	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$			-1	V
Base to emitter voltage	V_{BE}	$V_{CE} = -5 \text{ V}$, $I_B = -150 \text{ mA}$			-0.9	V
Gain bandwidth product	f_T	$V_{CE} = -5 \text{ V}$, $I_C = -150 \text{ mA}$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		20		pF

■ h_{FE} Classification

Marking	DH	DJ	DK
h_{FE}	60~120	100~200	160~320